# Advancement of High Power Laser Diodes for Pumping 2-micron Solid State Lasers

Farzin Amzajerdian, Byron Meadows, Michael Kavaya, Upendra Singh NASA Langley Research Center, MS 468, Hampton, Virginia 23681

## Nathaniel Baker

Lockheed Martin Engineering and Sciences Company, Hampton, Virginia

### Vikas Sudesh

Science and Technology Corporation, Hampton, Virginia

Abstract - The reliability and lifetime demanded by space-based applications of 2-micron solid state lasers are beyond the capability of currently available laser diode arrays. This paper provides the status of an ongoing technology advancement effort toward long-lifetime high power laser diode arrays suitable for pumping Thulium and Holmium based solid state lasers.

#### I. INTRODUCTION

Laser diode array is a critical component of any solid state laser systems and have been identified by NASA as a major risk area in deployment of laser remote sensing instruments in space. Laser diode arrays (LDAs) are used as the pump source for energizing the solid state lasing media to generate an intense coherent laser beam with a high spatial and spectral quality. The lifetime and reliability of laser remote sensing instruments are basically established by their pump laser diodes. Therefore, any improvement in their reliability will have a major impact on mission lifetime, risk, and cost. Unfortunately, limited commercial availability combined with lack of statistical data required for screening and predicating the reliability of high power laser diode arrays presented many challenges for past NASA laser missions. This led to establishing a task, addressing the laser diode issues, under the Laser Risk Reduction Project funded by NASA's Earth Science and Aerospace Enterprises. The laser diode task is being performed jointly by NASA/GSFC focusing on laser diodes used for pumping 1-micron solid state lasers and NASA/LaRC working on the laser diodes for 2-micron

The solid state laser design and the characteristics of its lasing materials define the operating wavelength, pulse duration, and power of the laser diodes. The pump requirements for high pulse energy 2-micron solid state lasers are substantially different from those of more widely used Neodymium based 1-micron lasers and in many aspects more challenging [1]. The 2-micron lasers require much longer pump pulse duration than 1-micron lasers, which causes the laser diode active material to experience drastic thermal cycling. This translates to a much shorter

lifetime compared to the laser diodes used for 1-micron lasers. In addition to the need for more reliable LDAs with longer lifetime, further improvement in the operational parameters of high power quasi-cw LDAs, such as electrical efficiency, brightness, and duty cycle, are also necessary for developing cost-effective 2-micron solid state laser instruments meeting the stringent size, heat dissipation, and power constraints of space. This paper discusses the current state of the 792 nm LDA technology and the technology areas being pursued toward improving their performance and reliability. This paper also reports the development of a characterization facility for addressing the specific issues associated with the LDAs for pumping 2-micron solid state lasers and provides the results of measurements to date on different laser diode packages.

#### II. 792 nm LDA TECHNOLOGY REQUIREMENTS

Recent advances in the development of high peak power quasi-CW LDAs in conductively-cooled packages will likely ease engineering problems resulting from physical and environmental constraints of space-based solid state lidar instruments. However, despite these advances, the LDAs meeting the pump requirements of Thulium and Holmium based solid state lasers still suffer from lifetime and reliability issues. High pulse energy 2-micron solid state lasers require high power quasi-CW LDAs with minimum pulse durations of one millisecond at 792 nm wavelength. Yet it is this relatively long pulse duration that is one of the main causes of limited lifetime for these arrays. Such relatively long pulse duration causes the laser diode active regions to experience high temperatures and drastic thermal cycling. Thermal cycling of the active regions is considered the primary reason for rapid rate of reduction of the LDA's power, and the excessive temperature rise is the leading suspect of premature failure [2]. The extreme temperature rise during the pulse can create considerable stress within the individual bars due to localized heating and various thermal mismatches between the bars, the substrate, and the bonding materials leading to premature failure. The thermally-induced rapid degradation can be improved to some extend by careful design of the laser head ensuring efficient extraction of heat from the laser diode bars and by operating the diodes at a power level considerably less than their maximum rating. In order to better address the lifetime and reliability issues and to improve the efficiency of these long-pulsewidth laser diode pump arrays, different laser diode packages are being investigated leading to the design and development of new packages with better thermal characteristics. Table 1 below summarizes the current state of 792 nm LDA technology and the goals defined based on the requirements of high pulse energy 2-micron lasers. As can be seen from Table 1, further technology advancement and better understanding of 792 LDA properties are needed before a long-lifetime 2micron lidar instrument can be launched. At the present time, there is no reliable data that can predict the long term operation of 792 nm LDAs.

TABLE 1. LDA REQUIREMENTS FOR PUMPING 2-µm SOLID STATE LASERS.

Parameter	Goal	Current State
Central Wavelength (nm)	792 +/- 1	792 +/- 3
Spectral Width (nm FWHM)	3	5
Peak Power Per Bar (W)	150	100
Pulse Width (msec)	1.5	1.0
Duty Cycle	3%	1%
Number of Bars	10	6
Bar Spacing (mm)	0.4	0.4
Electrical Efficiency	55%	45%
Wavelength Drift	+/- 1	Unknown
(nm/Bshots)		
Package	Conductively	Conductively
	Cooled	Cooled
Lifetime (number of shots)	$3 \times 10^9$	$<< 3 \times 10^9$

#### III. LDA CHARACTERIZATION

A Laser Diode Characterization Facility (LDCF) has been developed for evaluating the performance, reliability, and lifetime of various laser diode arrays under different operational conditions. The LDCF consists of two measurement stations: a Laser Diode Characterization Station and a Lifetime Test Station. The Characterization Station provides the basic characteristic parameters such as power, wavelength, linewidth, and efficiency. This setup is also capable of providing some specialized measurements that includes thermal profiling of laser diode facet and package, near and far field beam profiling, and highresolution spectral measurements. The Lifetime Test Station, as illustrated in Fig. 1, is capable of simultaneous measurement of 8 LDAs using a common set of instruments for accurate comparative analysis and evaluation. The Lifetime Test Station is fully automated using a single computer to set operational and environmental parameters. acquire and archive data, flag anomalous data, and generate a number of warning and status alert messages when necessary.

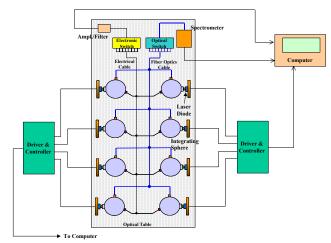


Figure 1. Laser diode array lifetime test setup.

An example of laser diode measurement is shown in Fig. 2 where the spectral characteristics of a conductively-cooled 6-bar array at 15 °C heatsink temperature is shown. The absorption spectrum of Tm, Ho;YLF laser material for s polarization is also shown for reference. Noteworthy is the wavelength shift and increase in spectral width with operating current which are also due to the laser diode junction temperature rise. Measuring the wavelength shift by varying the operating current or the pulse width is a common technique in indirectly determining the laser diode junction temperature and can be used for quantifying the critical thermal properties of different packages.

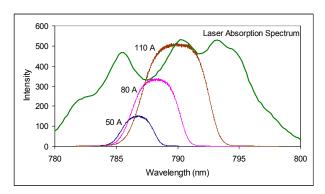


Figure 2. Spectral measurement of a 600-W conductively-cooled LDA.

#### IV. LDA PACKAGING TECHNOLOGY

As part of the effort to improve the lifetime and efficiency of laser diode pump arrays, a custom-designed package housing six 100W bars was fabricated by Cutting Edge Optronics, Inc. This experimental LDA (see Fig. 3) uses a diamond substrate and heatsink, as opposed to conventional BeO substrate and copper heatsink, for improved heat removal from the active regions of the bars. The heat rejection efficiency of this package was determined by

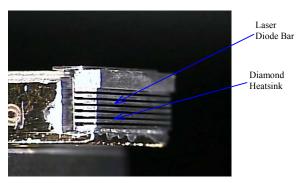


Figure 3. Diamond Package LDA.

running the array at a constant current and repetition rate of 80A and 10 Hz respectively, while measuring its output wavelength and electrical efficiency at different pulsewidths. Fig. 4 is an example of the measurement results showing the laser diode temperature rise as a function of dissipated heat in the package for the diamond package and a similar package with BeO substrate and copper heatsink. The slope of the temperature vs. heat curve provides a figure of merit, referred to as thermal resistance, for each package's heat rejection efficiency. The measurements of Fig. 4 indicate a reduction of about 17% in thermal resistance for the diamond package. This is significant as it can translate to substantial increase in laser lifetime. One might interpret 17% reduction in thermal resistance of diamond package as being equivalent to operating the Cu/BeO package at 17% lower power to achieve the same lifetime. Future plan includes simultaneous lifetime testing of the diamond package devices and the standard (BeO) array packages available commercially.

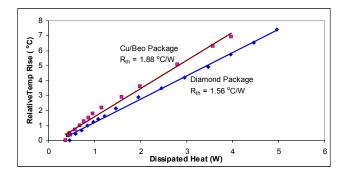


Figure 4. Thermal characteristics of 600-W LDAs in diamond and BeO/Cu packages.

#### REFERENCES

- [1] Jirong Yu, Alain Braud and Mulugeta Petros, "600 mJ, Double-pulsed 2-micron laser", Opt. Lett., Vol. 28, 540-542, 2003
- [2] N.I. Katsavets, et. al., "Study of correlation between optical characteristics and mirror facet temperature of the active region in high power SCH SQW InGaAs/GaAs and InGaAsP/GaAs laser diodes," SPIE Vol. 2148, 152-156, 1994.
- [3] M. A. Stephen and M. A. Krainak, "Qusi-CW laser diode bar life tests," SPIE Vol. 3244, 598-604, 1997.